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ABSTRACT OF THE DISCLOSURE

Various circuit devices, including diodes, and methods manufacturing therefor are provided. In one aspect, a method manufacturing is provided that includes forming a gate structure on a semiconductor portion of a substrate. The semiconductor portion has a first conductivity type. First and spacer structures are formed on opposite sides of the gate structure. A first impurity region of a second conductivity type is formed proximate the first spacer structure while the semiconductor portion lateral to the second spacer structure is masked. The first impurity region and the semiconductor portion define a junction. A width of the second spacer structure is reduced while the second spacer structure and the first impurity region are masked. A second impurity region of the first conductivity type is formed in the semiconductor portion proximate the second spacer structure. The method provides a diode with reduced series resistance.